

UTC UNISONIC TECHNOLOGIES CO., LTD

8550S

PNP SILICON TRANSISTOR

LOW VOLTAGE HIGH CURRENT SMALL SIGNAL PNP TRANSISTOR

DESCRIPTION

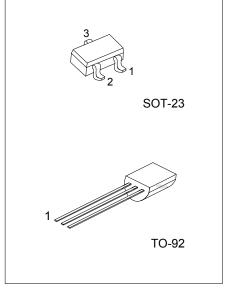
The UTC 8550S is a low voltage high current small signal PNP transistor, designed for Class B push-pull audio amplifier and general purpose applications.

FEATURES

*Collector current up to 700mA

*Collector-Emitter voltage up to 20 V

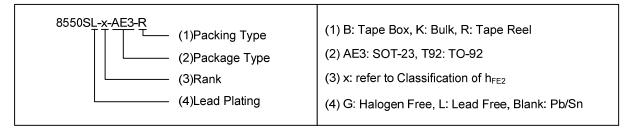
*Complimentary to 8050S



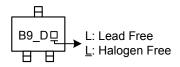
Lead-free: 8550SL Halogen-free: 8550SG

ORDERING INFORMATION

Ordering Number			Dookogo	Pin Assignment			Dooking	
Normal	Lead Free	Halogen-Free	Package	1	2	3	Packing	
8550S-x-AE3-R	8550SL-x-AE3-R	8550SG-x-AE3-R	SOT-23	Е	В	С	Tape Reel	
8550S-x-T92-B	8550SL-x-T92-B	8550SG-x-T92-B	TO-92	Е	С	В	Tape Box	
8550S-x-T92-K	8550SL-x-T92-K	8550SG-x-T92-K	TO-92	Е	С	В	Bulk	



MARKING (For SOT-23 Package)



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■ **ABSOLUTE MAXIMUM RATINGS** (Ta=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATING	UNITS
Collector-Base Voltage		V _{CBO}	-30	V
Collector-Emitter Voltage		V _{CEO}	-20	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		Ic	-700	mA
Collector Discinction/To-25°C)	SOT-23	J	350	mW
Collector Dissipation(Ta=25°C)	TO-92	Pc	1	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

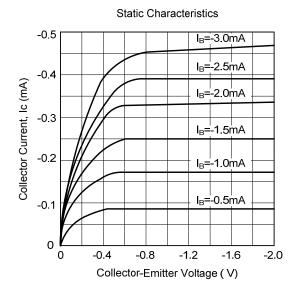
■ **ELECTRICAL CHARACTERISTICS** (Ta= 25°C, unless otherwise specified)

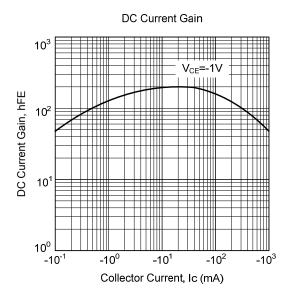
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100μA, I _E =0	-30			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I_C =-1mA, I_B =0	-20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-100\mu A, I_C=0$	-5			V
Collector Cut-off Current	I _{CBO}	V _{CB} =-30V, I _E =0			-1	μΑ
Emitter Cut-off Current	I _{EBO}	V_{EB} =-5 V , I_C =0			-100	nA
	h _{FE1}	V _{CE} =-1V, I _C =-1mA	100			
DC Current Gain	h _{FE2}	V _{CE} =-1V, I _C =-150 mA	120		400	
	h _{FE3}	V _{CE} =-1V, I _C =-500mA	40			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-500mA, I _B =-50mA			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I _C =-500mA, I _B =-50mA			-1.2	V
Base-Emitter Saturation Voltage	V _{BE}	V _{CE} =-1V, I _C =-10mA			-1.0	V
Current Gain Bandwidth Product	f⊤	V _{CE} =-10V, I _C =-50mA	100			MHz
Output Capacitance	Cob	V _{CB} =-10V, I _E =0, f=1MHz		9.0		pF

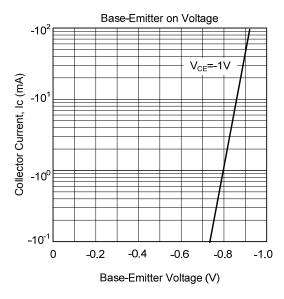
■ CLASSIFICATION OF h_{FE2}

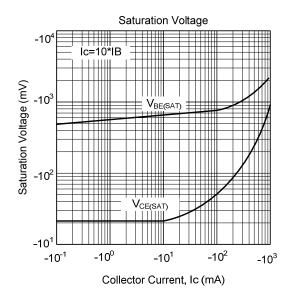
RANK	С	D	Е		
RANGE	120-200	160-300	280-400		

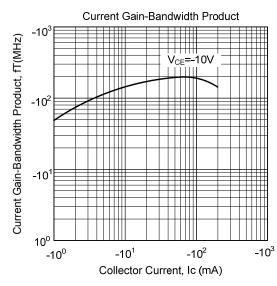
■ TYPICAL CHARACTERISTICS

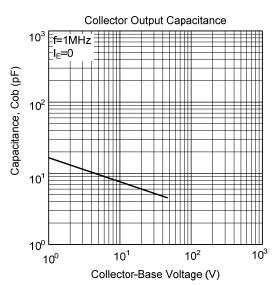












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